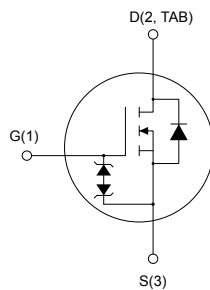
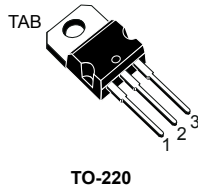


N-channel 800 V, 400 mΩ typ., 12 A MDmesh K5 Power MOSFET in a TO-220 package



AM01476v1_tab



Product status link

[STP14N80K5](#)

Product summary

Order code	STP14N80K5
Marking	14N80K5
Package	TO-220
Packing	Tube

Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STP14N80K5	800 V	445 mΩ	12 A

- Very low FoM (figure of merit)
- Ultra-low gate charge
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This very high voltage N-channel Power MOSFET is designed using MDmesh K5 technology based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance and ultra-low gate charge for applications requiring superior power density and high efficiency.

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	800	V
V_{GS}	Gate-source voltage	± 30	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	12	A
	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	7.4	
$I_{DM}^{(1)}$	Drain current (pulsed)	48	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	130	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	4.5	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	50	
T_{stg}	Storage temperature range	-55 to 150	$^{\circ}\text{C}$
T_J	Operating junction temperature range		

1. Pulse width is limited by safe operating area.
2. $I_{SD} \leq 12\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$; $V_{DS(peak)} < V_{(BR)DSS}$, $V_{DD} = 640\text{ V}$.
3. $V_{DD} \leq 640\text{ V}$

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.96	$^{\circ}\text{C}/\text{W}$
R_{thJA}	Thermal resistance, junction-to-ambient	62.5	

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
$I_{AR}^{(1)}$	Avalanche current, repetitive or not repetitive	4	A
$E_{AS}^{(2)}$	Single pulse avalanche energy	270	mJ

1. Pulse width limited by T_J max.
2. Starting $T_J = 25\text{ }^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$.

2 Electrical characteristics

$T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	800			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 800\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 800\text{ V}$, $T_C = 125\text{ }^{\circ}\text{C}$ ⁽¹⁾			50	
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 100\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 6\text{ A}$		400	445	m Ω

1. Specified by design, not tested in production.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	620	-	pF
C_{oss}	Output capacitance		-	60	-	
C_{rss}	Reverse transfer capacitance		-	0.8	-	
$C_{o(tr)}^{(1)}$	Time-related equivalent capacitance	$V_{DS} = 0\text{ to }640\text{ V}$, $V_{GS} = 0\text{ V}$	-	107	-	pF
$C_{o(er)}^{(2)}$	Energy-related equivalent capacitance		-	39	-	
R_g	Intrinsic gate resistance	$f = 1\text{ MHz}$, $I_D = 0\text{ A}$	-	6.5	-	Ω
Q_g	Total gate charge	$V_{DD} = 640\text{ V}$, $I_D = 12\text{ A}$, $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 15. Test circuit for gate charge behavior)	-	22	-	nC
Q_{gs}	Gate-source charge		-	4.3	-	
Q_{gd}	Gate-drain charge		-	16.5	-	

1. $C_{o(tr)}$ is a constant capacitance value that gives the same charging time as C_{oss} while V_{DS} is rising from 0 V to the stated value.

2. $C_{o(er)}$ is a constant capacitance value that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 V to the stated value.

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 400\text{ V}$, $I_D = 6\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 14. Test circuit for resistive load switching times and Figure 19. Switching time waveform)	-	12.5	-	ns
t_r	Rise time		-	8	-	
$t_{d(off)}$	Turn-off delay time		-	33	-	
t_f	Fall time		-	10	-	

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		12	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		48	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 12\text{ A}$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 12\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$ (see Figure 16. Test circuit for inductive load switching and diode recovery times)	-	365		ns
Q_{rr}	Reverse recovery charge		-	4.77		μC
I_{RRM}	Reverse recovery current		-	26		A
t_{rr}	Reverse recovery time	$I_{SD} = 12\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ (see Figure 16. Test circuit for inductive load switching and diode recovery times)	-	485		ns
Q_{rr}	Reverse recovery charge		-	5.85		μC
I_{RRM}	Reverse recovery current		-	24		A

1. Pulse width is limited by safe operating area.

2. Pulse test: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

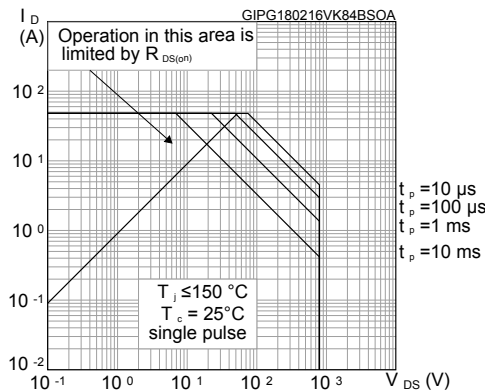


Figure 2. Normalized transient thermal impedance

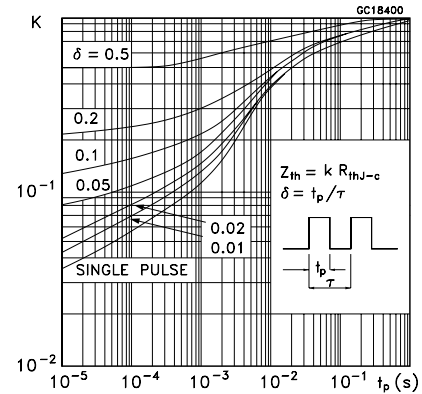


Figure 3. Typical output characteristics

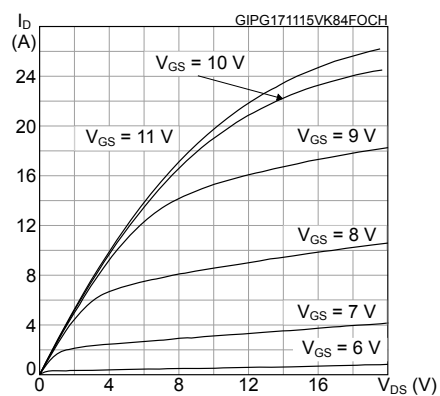


Figure 4. Typical transfer characteristics

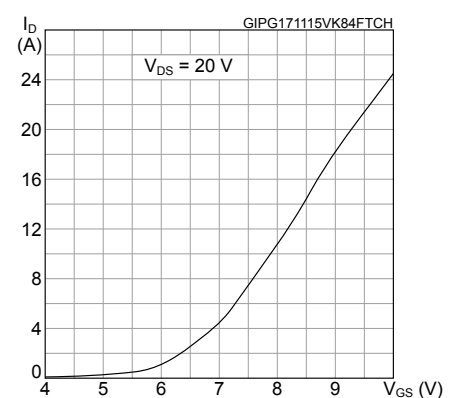


Figure 5. Typical gate charge characteristics

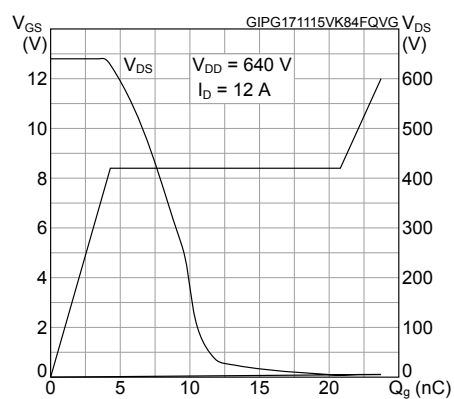


Figure 6. Typical drain-source on-resistance

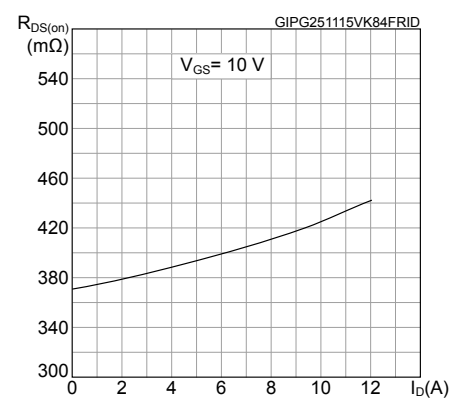


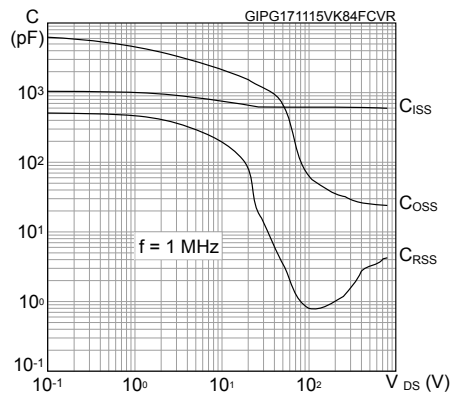
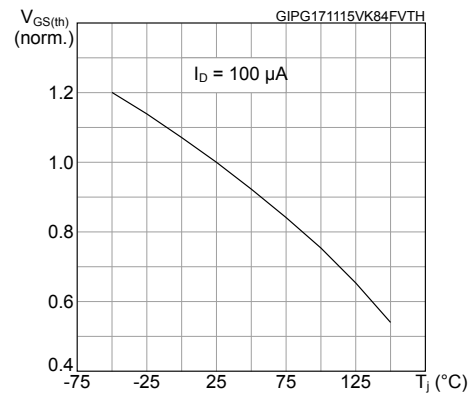
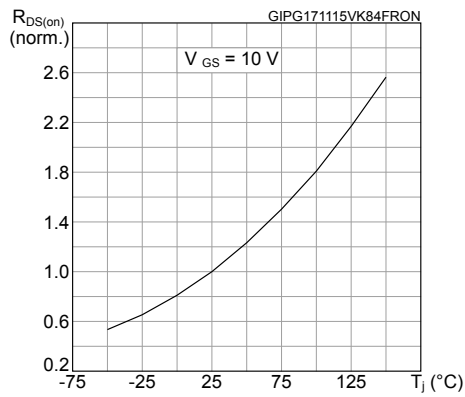
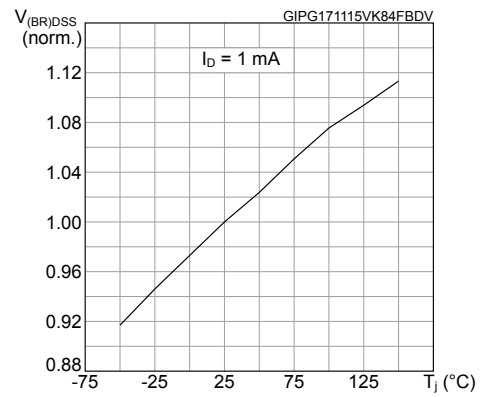
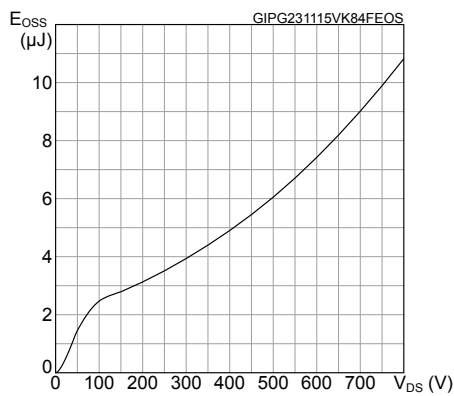
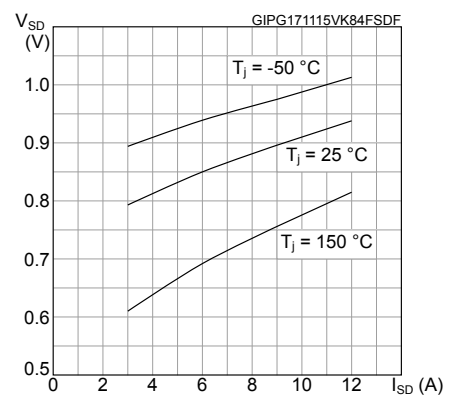
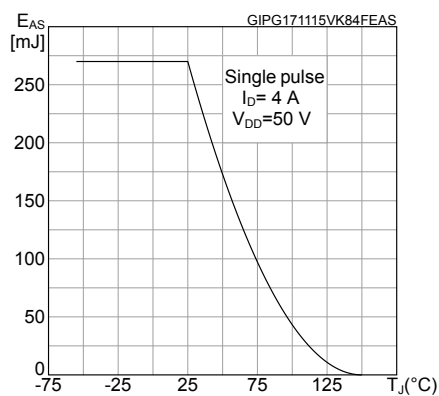
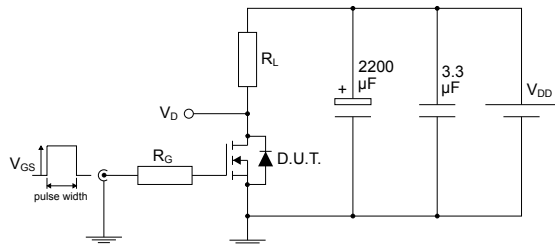
Figure 7. Typical capacitance characteristics

Figure 8. Normalized gate threshold vs temperature

Figure 9. Normalized on-resistance vs temperature

Figure 10. Normalized breakdown voltage vs temperature

Figure 11. Typical output capacitance stored energy

Figure 12. Typical reverse diode forward characteristics


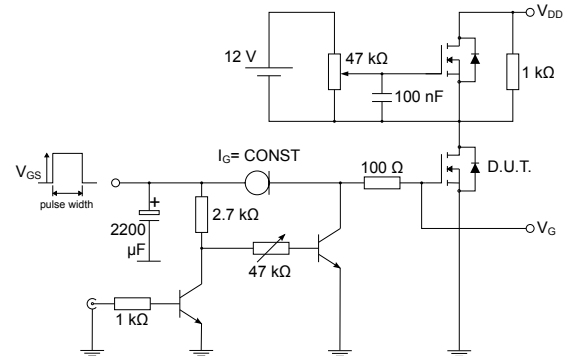
Figure 13. Maximum avalanche energy vs temperature



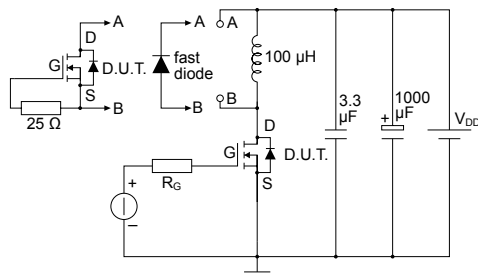
3 Test circuits

Figure 14. Test circuit for resistive load switching times


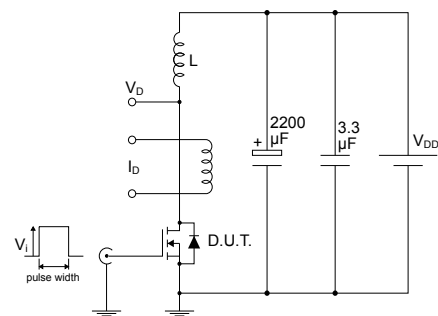
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Figure 15. Test circuit for gate charge behavior


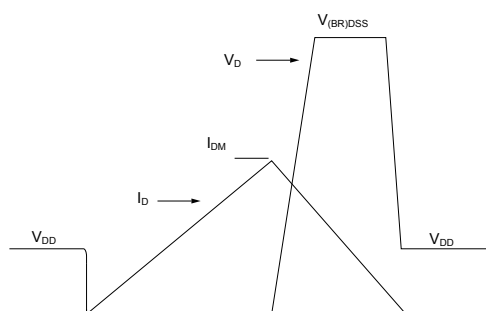
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Figure 16. Test circuit for inductive load switching and diode recovery times


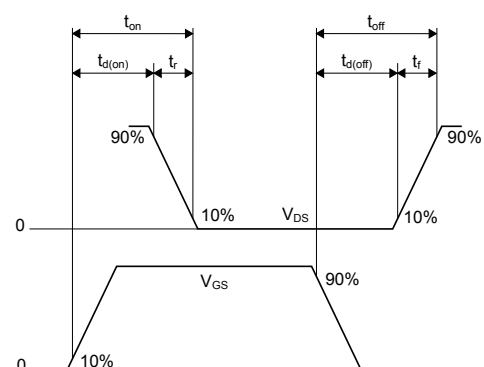
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Figure 17. Unclamped inductive load test circuit


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Figure 18. Unclamped inductive waveform


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Figure 19. Switching time waveform


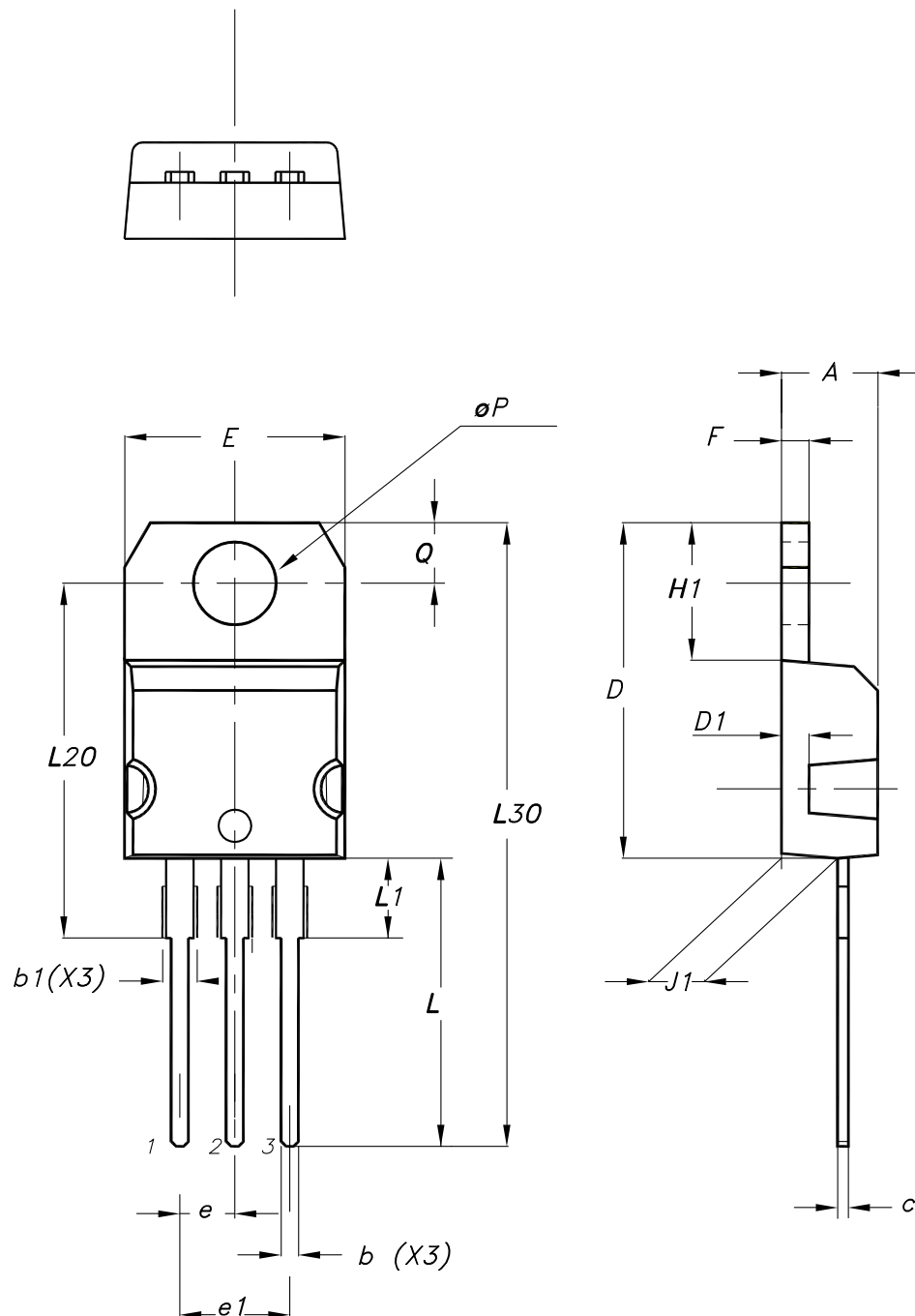
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4 Package information

To meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-220 type A package information

Figure 20. TO-220 type A package outline



0015988_typeA_Rev_24

Table 8. TO-220 type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95
Slug flatness		0.03	0.10

Revision history

Table 9. Document revision history

Date	Revision	Changes
04-Mar-2016	1	First release.
16-Mar-2026	2	Updated Section 4.1: TO-220 type A package information . Minor text changes.

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